

2-Input NAND Gate with Open Drain Output

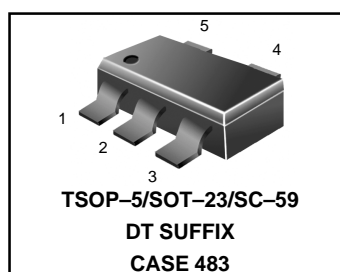
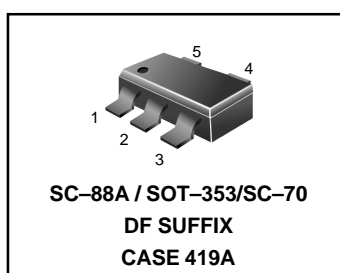
MC74VHC1G03

The MC74VHC1G03 is an advanced high speed CMOS 2-input NOR gate with an open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including an open drain output which provides the capability to set output switching level. This allows the MC74VHC1G03 to be used to interface 5 V circuits to circuits of any voltage between V_{CC} and 7 V using an external resistor and power supply.

The MC74VHC1G03 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage.

- High Speed: $t_{PD} = 3.6$ ns (Typ) at $V_{CC} = 5$ V
- Low Internal Power Dissipation: $I_{CC} = 2$ mA (Max) at $T_A = 25^\circ\text{C}$
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16



MARKING DIAGRAMS

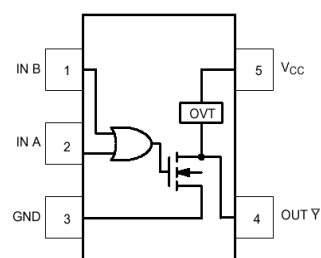
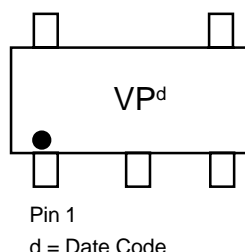
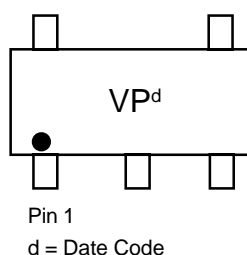


Figure 1. Pinout (Top View)

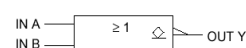


Figure 2. Logic Symbol

PIN ASSIGNMENT	
1	IN B
2	IN A
3	GND
4	OUT \bar{Y}
5	V_{CC}

Inputs		Output
A	B	\bar{Y}
L	L	Z
L	H	L
H	L	L
H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74VHC1G03

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	- 0.5 to + 7.0	V
V_{IN}	DC Input Voltage	- 0.5 to 7.0	V
V_{OUT}	DC Output Voltage	$V_{CC}=0$ High or Low State	- 0.5 to 7.0 -0.5 to $V_{CC} + 0.5$
I_{IK}	Input Diode Current	-20	mA
I_{OK}	Output Diode Current	$V_{OUT} < GND; V_{OUT} > V_{CC}$	+20
I_{OUT}	DC Output Current, per Pin	+ 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND	+50	mA
P_D	Power dissipation in still air	SC-88A, TSOP-5	200
θ_{JA}	Thermal resistance	SC-88A, TSOP-5	333
T_L	Lead Temperature, 1 mm from Case for 10 s		260
T_J	Junction Temperature Under Bias		+ 150
T_{stg}	Storage temperature		-65 to +150
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 > 200 N/A
$I_{LATCH-UP}$	Latch-Up Performance	Above V_{CC} and Below GND at 125°C (Note 5)	± 500

1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.
2. Tested to EIA/JESD22-A114-A
3. Tested to EIA/JESD22-A115-A
4. Tested to JESD22-C101-A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	5.5	V
V_{IN}	DC Input Voltage	0.0	5.5	V
V_{OUT}	DC Output Voltage	0.0	7.0	V
T_A	Operating Temperature Range	- 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 3.3 \pm 0.3$ V $V_{CC} = 5.0 \pm 0.5$ V	0 0	100 20

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

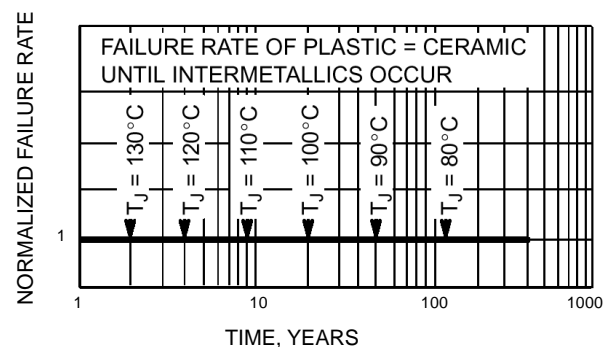


Figure 3. Failure Rate vs. Time
Junction Temperature

MC74VHC1G03
DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0	1.5			1.5		1.5		V
			3.0	2.1			2.1		2.1		
			4.5	3.15			3.15		3.15		
			5.5	3.85			3.85		3.85		
V _{IL}	Maximum Low-Level Input Voltage		2.0			0.5		0.5		0.5	V
			3.0			0.9		0.9		0.9	
			4.5			1.35		1.35		1.35	
			5.5			1.65		1.65		1.65	
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	2.0	1.9	2.0		1.9		1.9		V
			3.0	2.9	3.0		2.9		2.9		
			4.5	4.4	4.0		4.4		4.4		
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0	2.58			2.48		2.34		
			4.5	3.94			3.80		3.66		
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0		0.0	0.1		0.1		0.1	V
			3.0		0.0	0.1		0.1		0.1	
			4.5		0.0	0.1		0.1		0.1	
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0			0.36		0.44		0.52	
			4.5			0.36		0.44		0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μA
I _{OPD}	Maximum Off-state Leakage Current	V _{OUT} = 5.5 V	0			0.25		2.5		5.0	μA

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input t_r = t_f = 3.0 ns

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55°C to 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PZL}	Maximum Output Enable Time, Input A or B to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF R _L = R _I = 500 Ω C _L = 50 pF		5.6	7.9		9.5		11.0	ns
				8.1	11.4		13.0		15.5	
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF R _L = R _I = 500 Ω C _L = 50 pF		3.6	5.5		6.5		8.0	
				5.1	7.5		8.5		10.0	
t _{PLZ}	Maximum Output Disable Time	V _{CC} = 3.3 ± 0.3 V C _L = 50 pF R _L = R _I = 500 Ω		8.1	11.4		13.0		15.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 50 pF R _L = R _I = 500 Ω		5.1	7.5		8.5		10.0	
C _{IN}	Maximum Input Capacitance			4	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V		
C _{PD}	Power Dissipation Capacitance (Note 6)	18		pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} × V_{CC} × f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} × V_{CC}² × f_{in} + I_{CC} × V_{CC}.

MC74VHC1G03

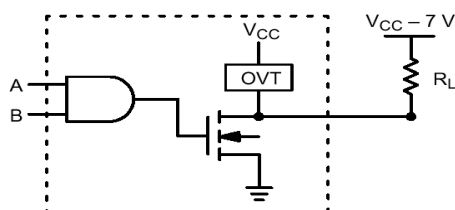


Figure 4. Output Voltage Mismatch Application

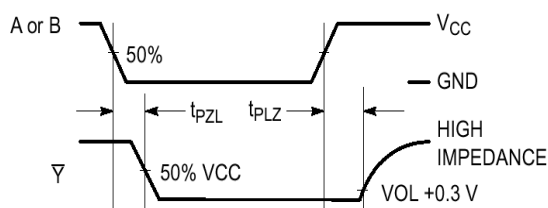


Figure 5. Switching Waveforms

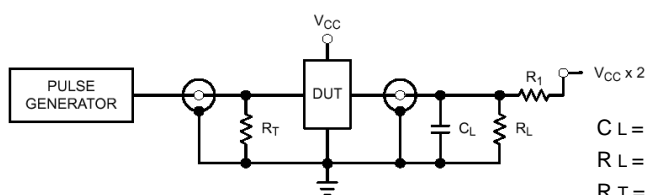


Figure 6. Test Circuit

$C_L = 50 \text{ pF}$ equivalent (Includes jig and probe capacitance)
 $R_L = R_1 = 500 \Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

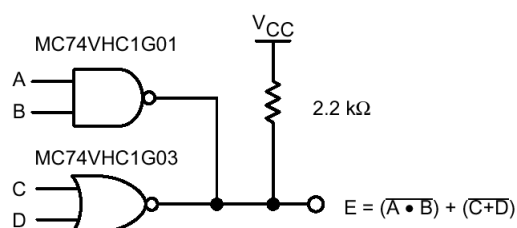


Figure 7. Complex Boolean Functions

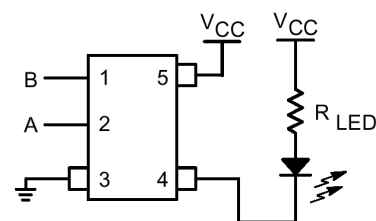


Figure 8. LED Driver

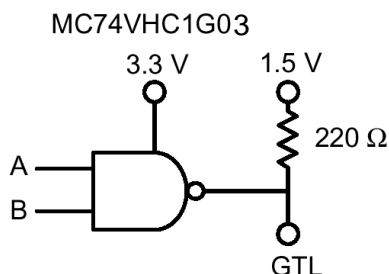


Figure 9. GTL Driver

DEVICE ORDERING INFORMATION

Device Nomenclature								
Device Order Number	Logic Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix	Package Type (Name/SOT#/Common Name)	Tape and Reel Size
MC74VHC1G03DFT1	MC	74	VHC1G	03	DF	T1	SC-70/SC-88A/SOT-353	178 mm (7 in) 3000 Unit
MC74VHC1G03DFT2	MC	74	VHC1G	03	DF	T2	SC-70/SC-88A/SOT-353	178 mm (7 in) 3000 Unit
MC74VHC1G03DFT4	MC	74	VHC1G	03	DF	T4	SC-70/SC-88A/SOT-353	330 mm (13 in) 10,000 Unit
MC74VHC1G03DTT1	MC	74	VHC1G	03	DT	T1	SOT-23/TSOPS/SC-59	178 mm (7 in) 3000 Unit
MC74VHC1G03DTT3	MC	74	VHC1G	03	DT	T3	SOT-23/TSOPS/SC-59	330 mm (13 in) 10,000 Unit